

SMART SENSORS

Dr. H. K. Verma

Distinguished Professor (EEE)
Sharda University, Greater Noida

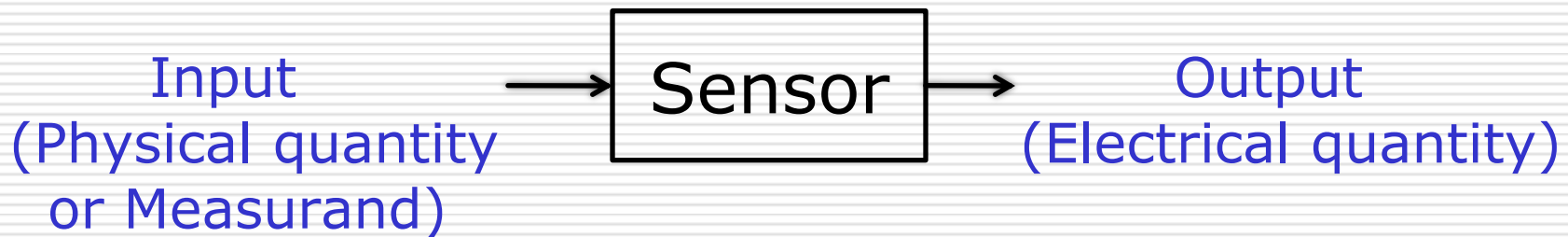
(Formerly: Deputy Director and Professor of Instrumentation
Indian Institute of Technology Roorkee)

Expert Lecture delivered at:
Gautam Buddha University
Greater Noida (UP)
on 19th April, 2016

Smart-Sensor Basics

What is a Sensor?

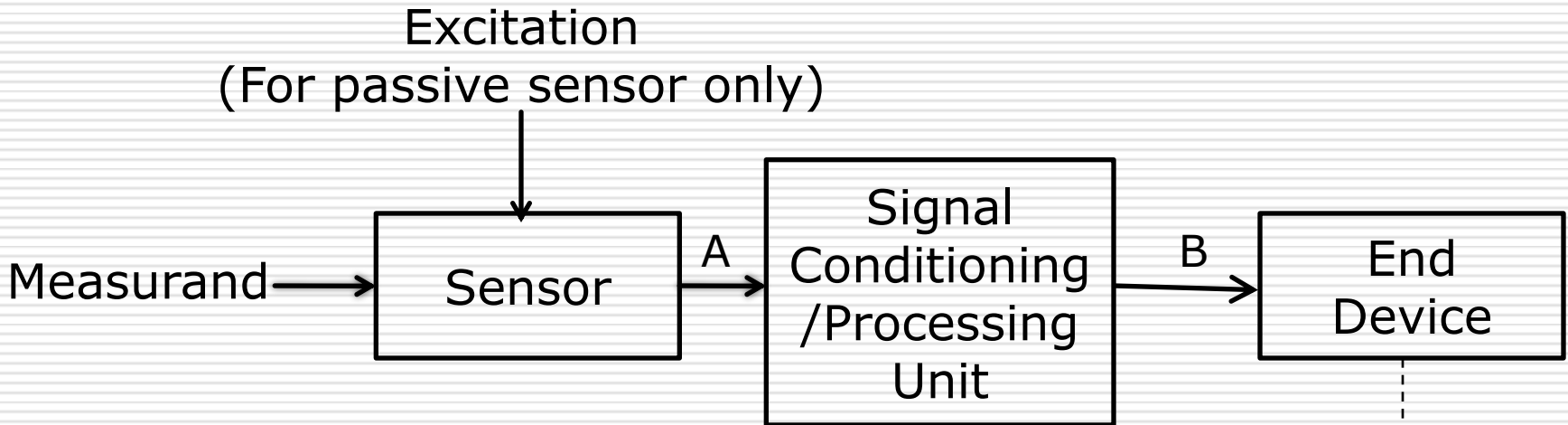
- ❖ Device that senses a **physical quantity**
- ❖ This physical quantity becomes **input** to the sensor
- ❖ **Output** of the sensor is an electrical quantity
- ❖ Input is called measured quantity or “**measurand**”



Sensor Output

- ❖ The electrical output of a sensor can be one of the two types:
 - ***Variation of an electrical parameter***
 - ***An electrical signal***
- ❖ Variation of electrical parameter means
 - Variation of resistance (ΔR), or
 - Variation of inductance (ΔL), or
 - Variation of capacitance (ΔC)
- ❖ Electrical signal means
 - Voltage signal, or
 - Current signal

Sensor-Based Measurement System



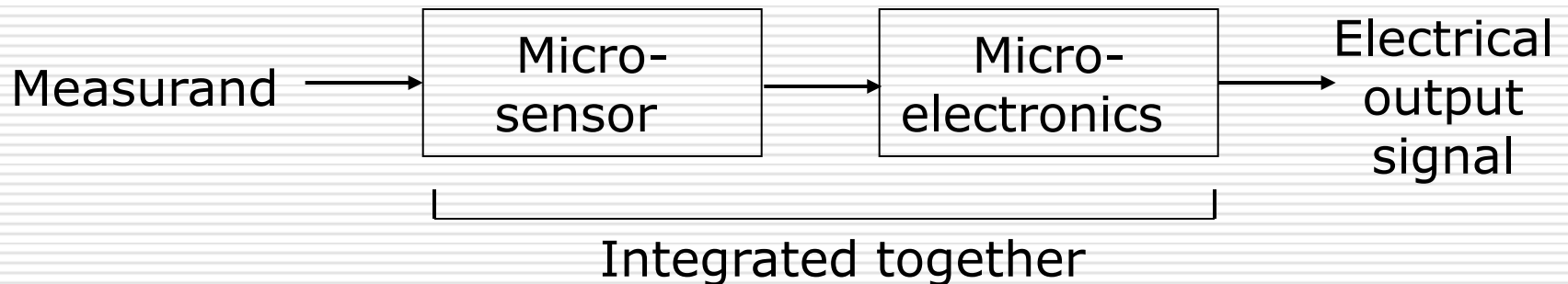
Conditions or processes electrical signal A into signal B to make it compatible with End Device, **both in form and magnitude.**

- Indicating device
- Display device
- Storage device
- Comm. device
- Data processor

What is a Smart Sensor?

- Most of the sensors now *labeled as Smart Sensors* by the manufacturers and *accepted as Smart Sensors* by the users would fit into the following definition:

“Smart Sensor is a micro-sensor suitably integrated with appropriate micro-electronics, such that the final output is fully or easily compatible with the intended end device or devices”

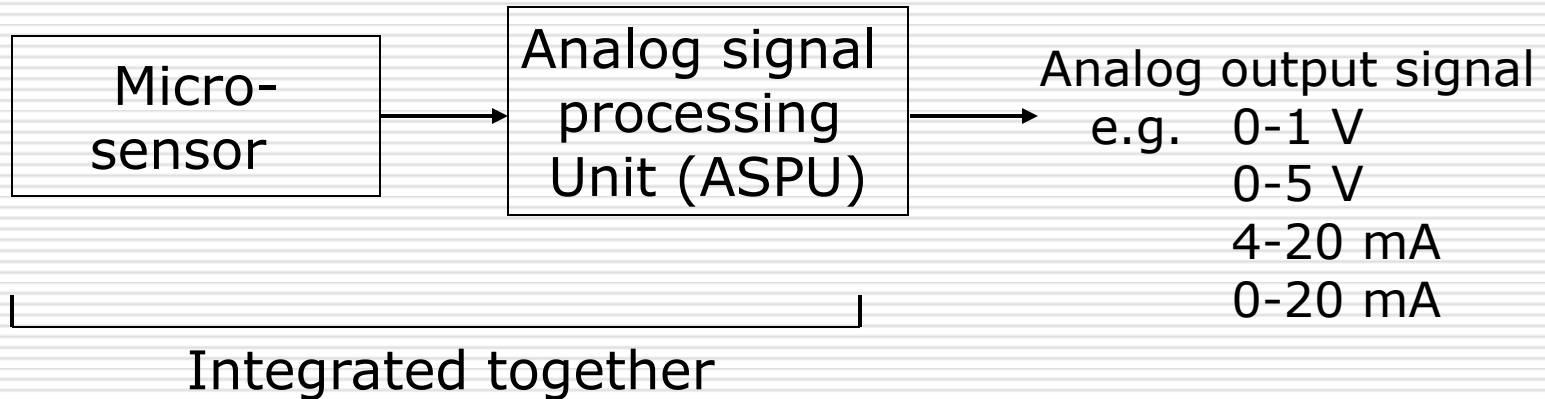


Levels of Integration

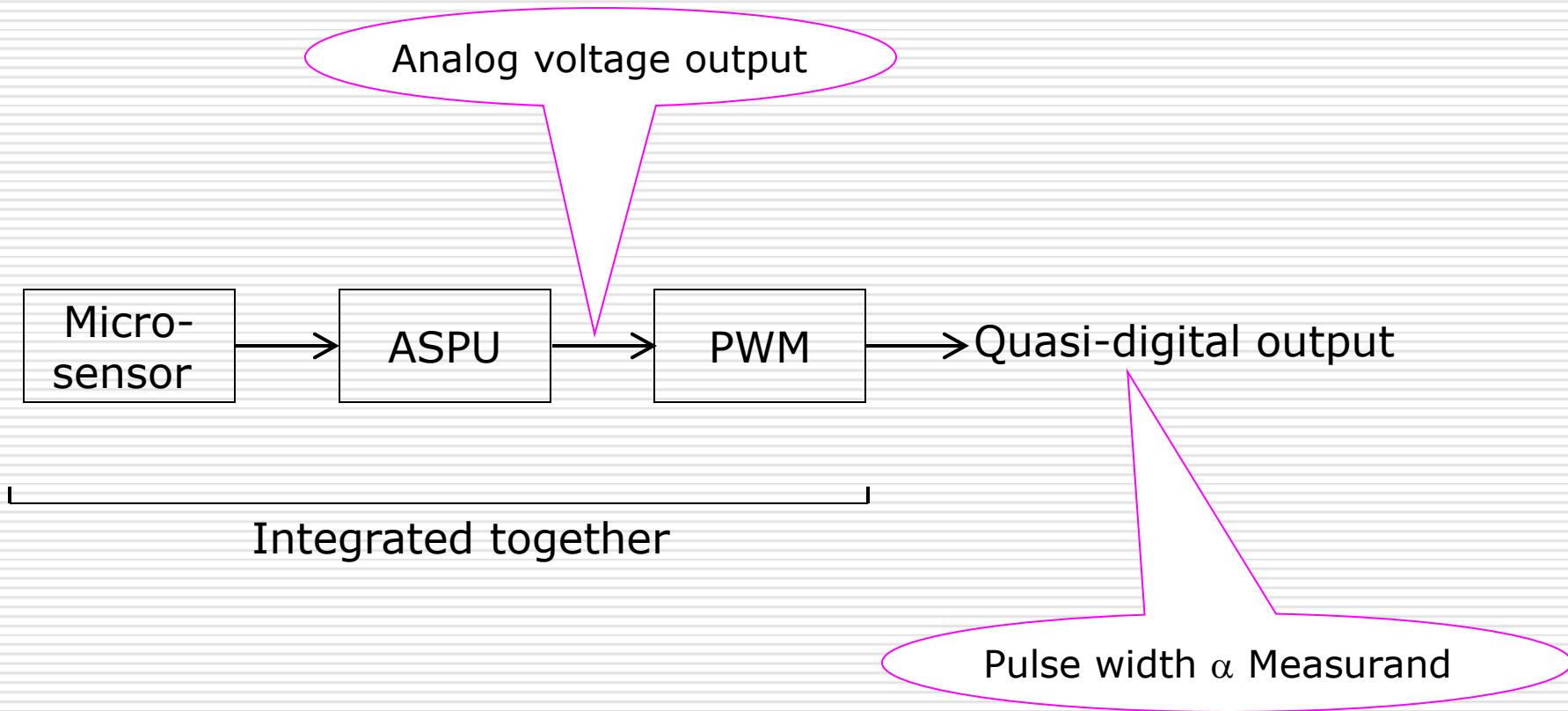
- ❖ The output signal of smart sensor can have one of three forms:
 - Analog
 - Digital
 - Quasi-digital (PWM or pulse frequency)

- ❖ Extent/ level of integration of electronics with the micro-sensor:
 - Lowest Level: Smart sensor with analog output
 - Low Level: Smart sensor with quasi-digital output
 - High Level: Smart sensor with digital output
 - Higher Level: Smart intelligent sensor
 - Highest Level: Smart network sensor

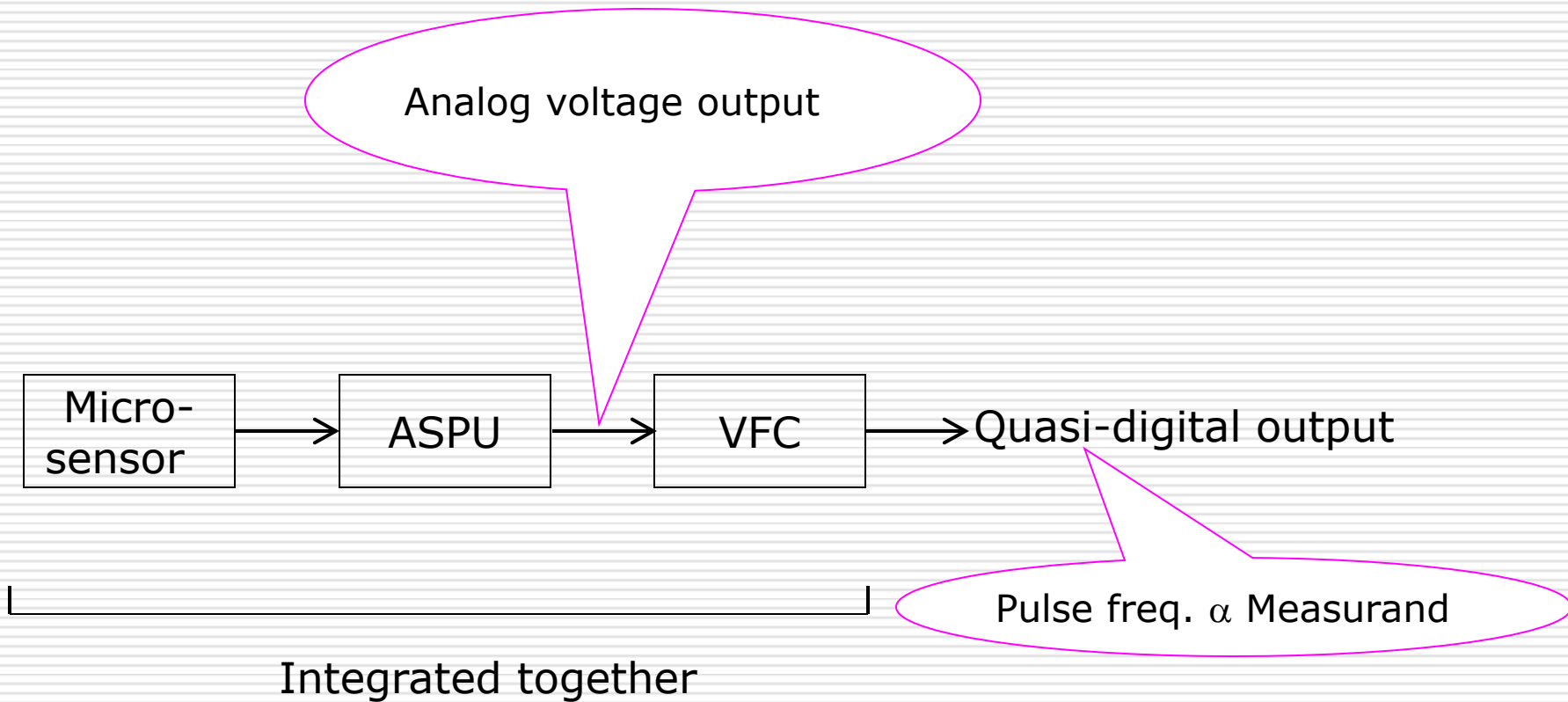
Smart Sensor with Analog Output



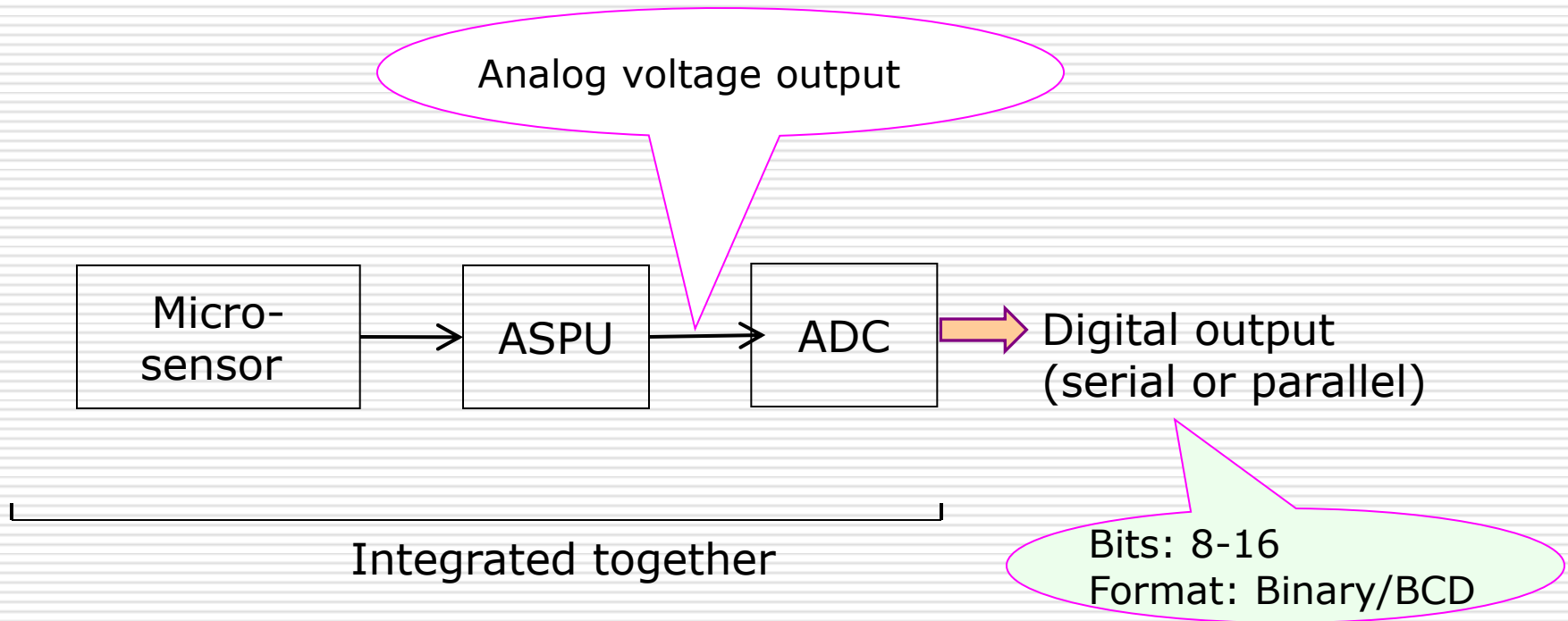
Smart Sensor with PWM Output



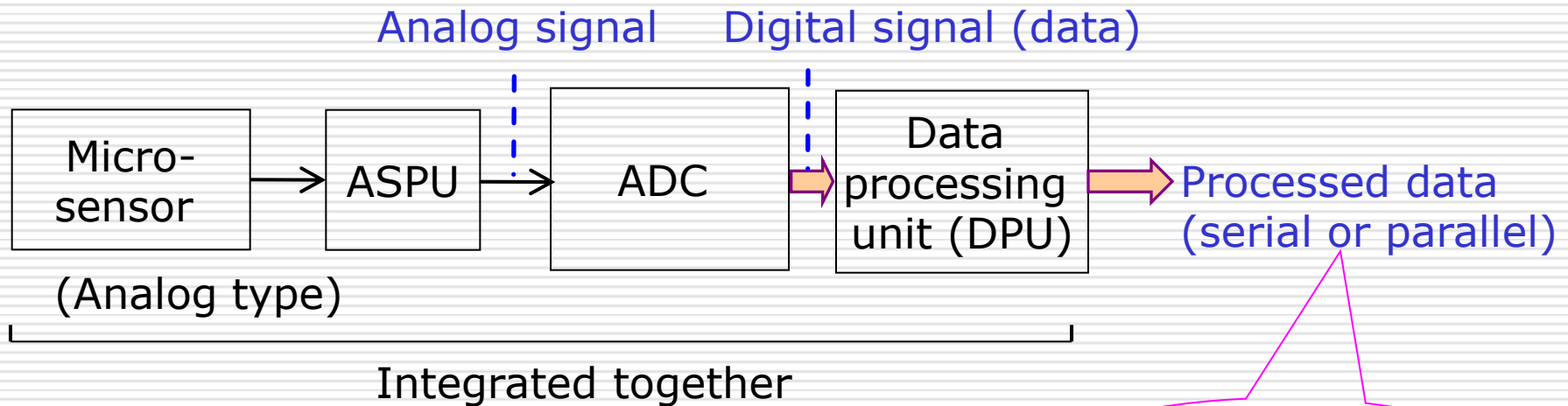
Smart Sensor with Pulse-Frequency Output



Smart Sensor with Digital Output



Smart Intelligent Sensor



DPU = Microcontroller

OR

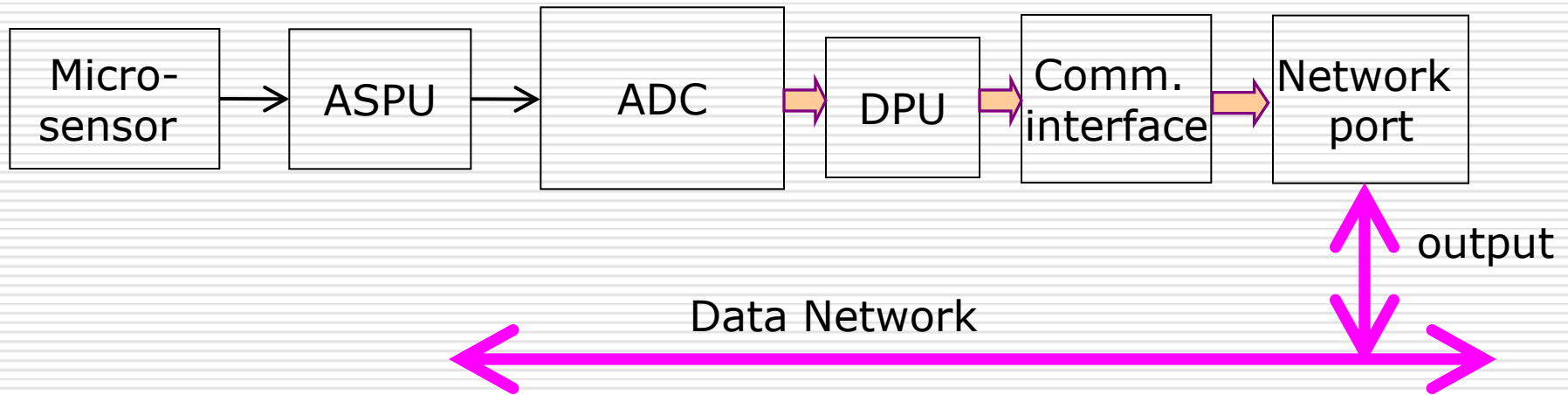
μ P + memory + I/O interface

OR

DSP + memory + I/O interface

Can be readily connected to a host computer or other digital system

Smart Network Sensor



Output: processed data on integrated network port in appropriate format

Advantages of Smart Sensor (1)

1. User's Convenience because of:

- No wiring
- Compact size
- No headache of selecting SC
- No headache of designing SC

2. Superior Performance because:

- Externally-induced noise absent, high SNR
- Built-in sensor-specific SC circuits perform better
- Built-in negative feedback reduces nonlinearity
- Built-in compensating circuits reduce sensitivity to temperature/ excitation changes

Advantages of Smart Sensor (2)

3. High Reliability because of:

- Reduced component count
- Reduced wiring

4. Cost Reduction because of:

- Concurrent production of electronics and sensor
- Mass production techniques

Additional Advantages of Smart Intelligent Sensor

- ❑ Performance Improvement because of:
 - Linearization of response using software
 - Reduction of cross-sensitivity using software
 - Automatic self calibration
- ❑ Simpler Interfacing because:
 - Data formatting can be done as per need
- ❑ Internal Data Logging because of:
 - On-chip EEPROM or flash-RAM
- ❑ Higher flexibility because:
 - Most of functions are software-based.

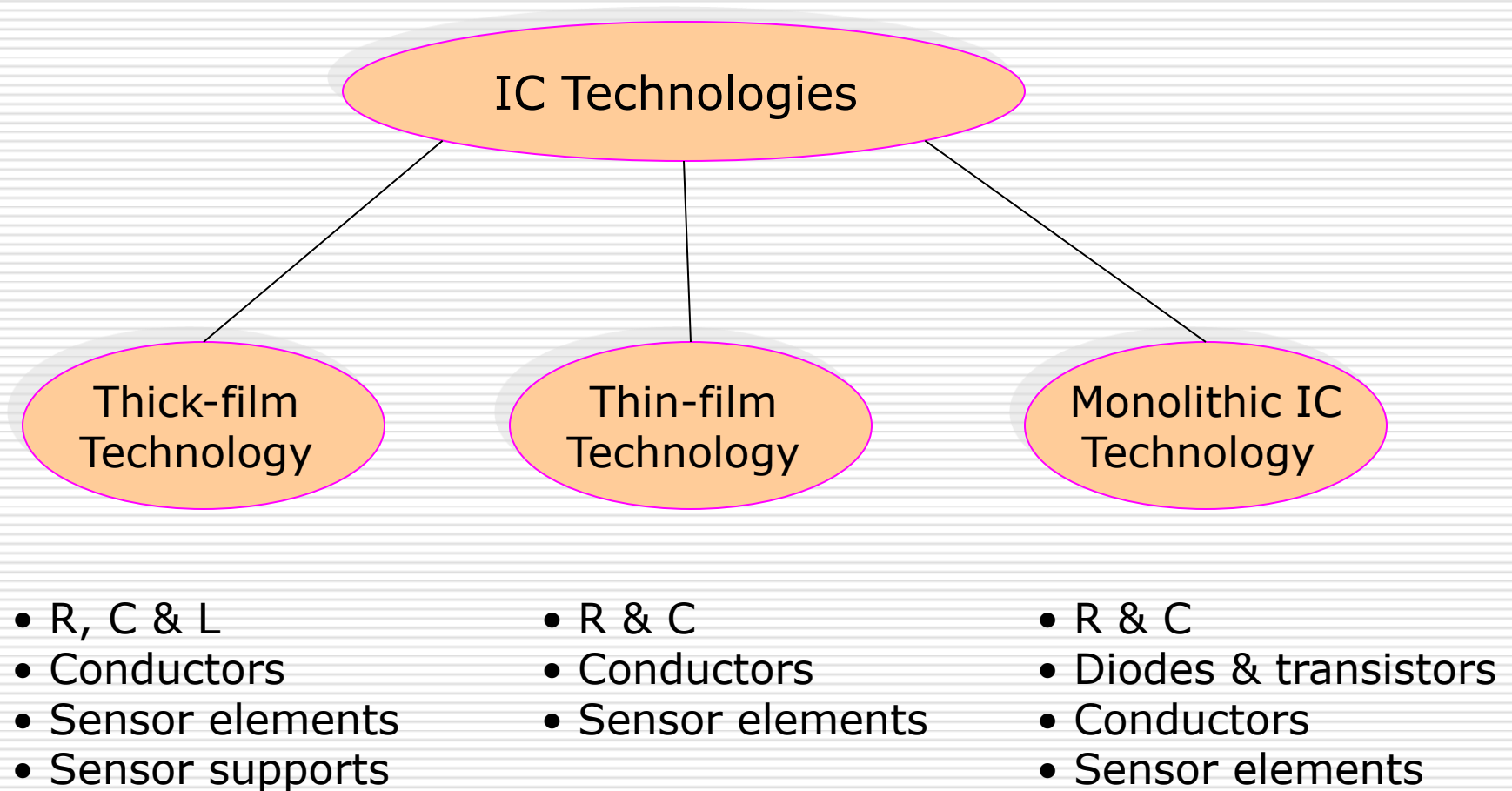
Smart-Sensor Technologies

Smart Sensor Technologies

Two types of technologies used:

- ❑ IC Technologies
- ❑ Micromachining Technologies

IC Technologies & Capabilities



Thick-Film Sensor Elements

- ❑ Temperature Sensors: Film RTD
 - Film thermistor
 - Film thermocouple

- ❑ Pressure Sensors: Film diaphragms
 - Film capacitors
 - Piezo-electric pastes
 - Piezo-resistive pastes

- ❑ Light Sensors: Photo-conductive pastes

- ❑ Magnetic Sensors: Magneto-resistive pastes

- ❑ Humidity Sensors: Organic polymer based pastes

- ❑ Gas Sensors: Metal-oxide pastes

Advantages of Thick Film Technology

- ❑ Components can withstand high temperatures
- ❑ Large voltage / current excitation can be used
- ❑ Heaters can be integrated
- ❑ Economical for low-volume production

Thin-Film Deposition Techniques

- Sputtering or cathodic deposition
- Vacuum evaporation
- Spin casting
- Reactive growth
- Chemical vapour deposition
- Plasma deposition

Thin-Film Materials

- ❑ For conductors: Aluminium or gold
- ❑ For resistors: Nichrome
- ❑ For dielectrics: Silicon dioxide
- ❑ For sensors (examples)
 - Strain gauge: Nichrome, polycrystalline silicon
 - RTD: Platinum
 - Gas sensor: Zinc oxide
 - Piezo-resistive pressure sensor: Nichrome, polycrystalline silicon
 - Thermo-anemometric flow sensor: Gold

Advantages of Thin-Film Technology

- ❑ Almost any metal can be deposited to produce thin-film sensors
- ❑ Add resistances, capacitances and sensors to monolithic IC.
- ❑ Miniaturization (smaller dimensions than thick-film devices).
- ❑ Economical for high-volume production.

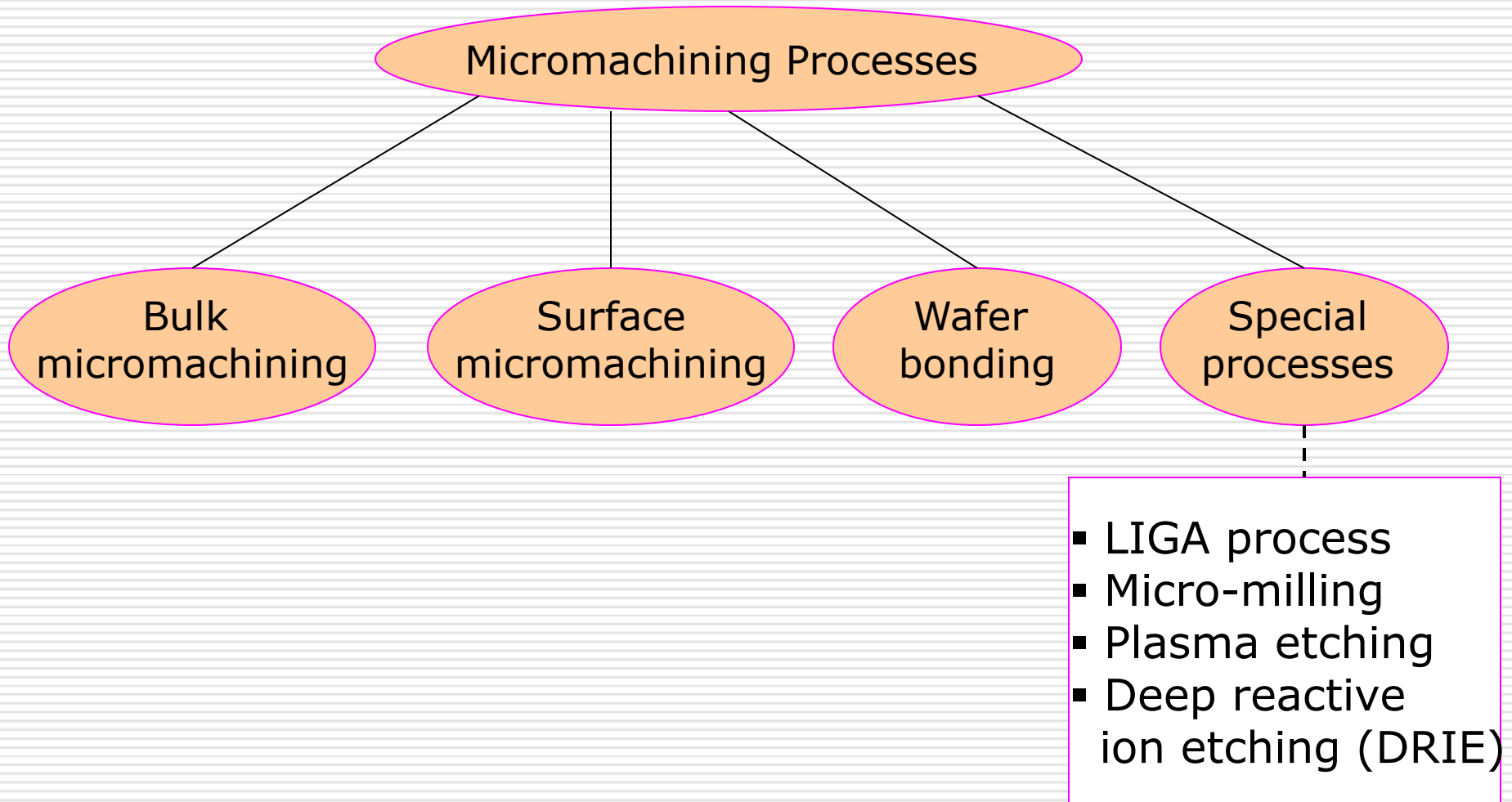
Monolithic IC Technology: Advantages

- Both active and passive devices
- Very high density of devices

Monolithic IC Technology: Limitations

- A few types of sensors only
- Resistances in medium-range only
- Capacitances of small values only

Micromachining Technologies



Bulk Micromachining

- ❑ Si wafer is etched on both sides
- ❑ Etching done with masks and etchants
- ❑ Pattern defined by photo-lithographic technique
- ❑ Etching processes:
 - Isotropic etching
 - Anisotropic etching

Isotropic Etching

- ❑ Etchants used have same etching rate for all crystallographic orientations of silicon wafer (crystal)

- ❑ Common Etchants (examples)
 - Sulfur hexafluoride (SF₆)
 - Hydrogen fluoride (HF)

- ❑ Structures Produced (examples)
 - Semi-spherical cavity
 - Rim-cantilever

Anisotropic Etching

- ❑ Etchants used have **different** etching rates for different crystallographic orientations of silicon wafer (crystal)

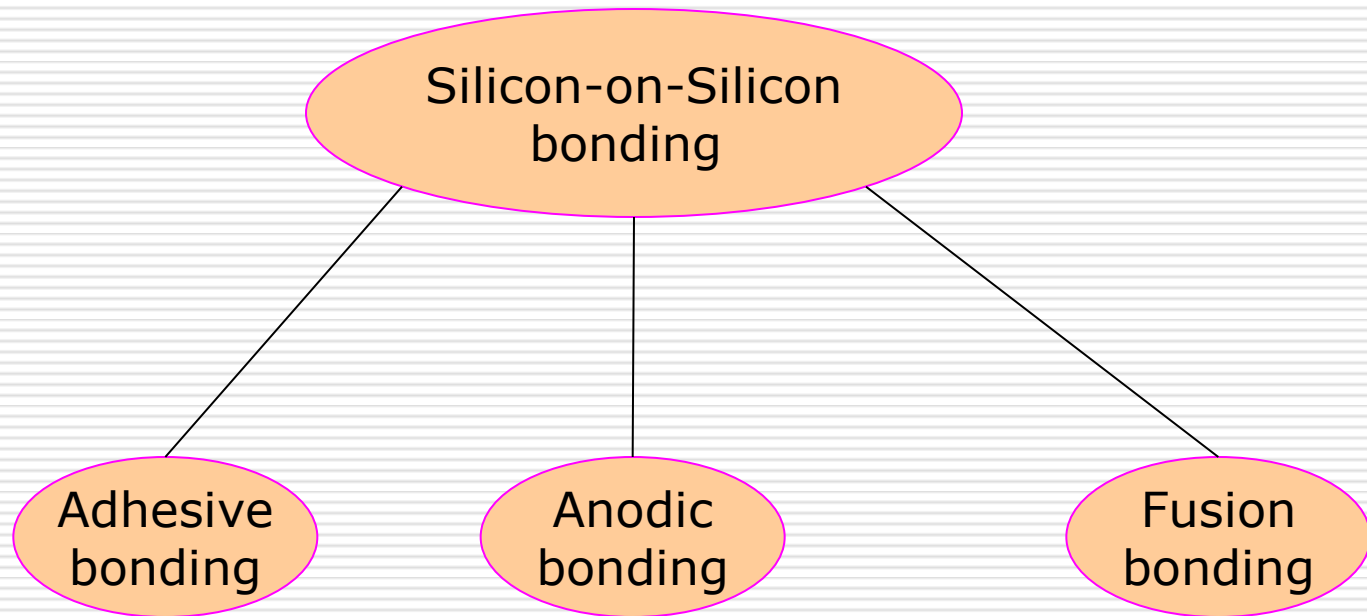
- ❑ Common Etchants (examples)
 - Ethylene-diamine pyrocatechol (EDP)
 - Potassium hydroxide (KOH)

- ❑ Structures Produced (example)
 - Diaphragm

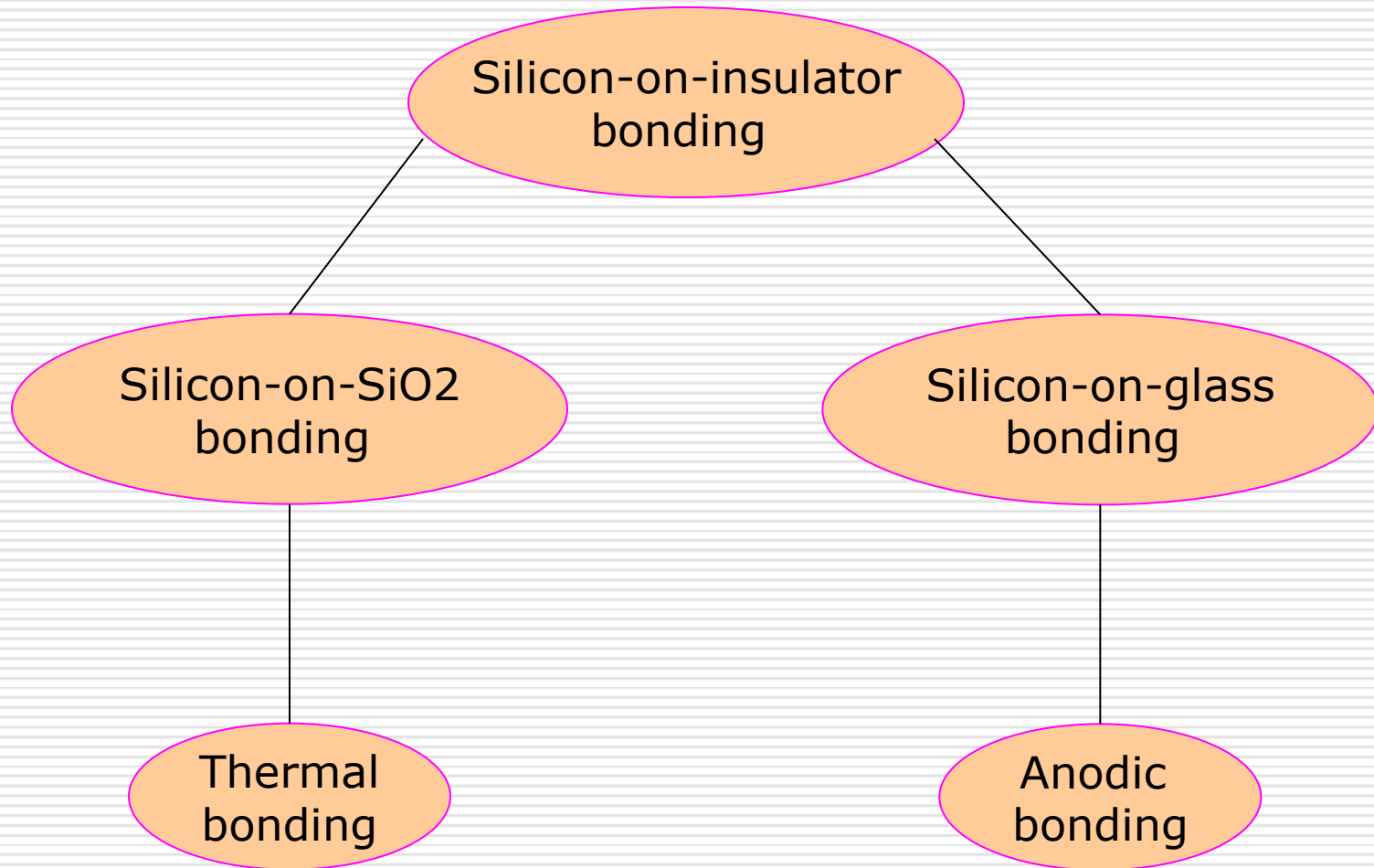
Surface Micromachining

- ❑ Etching and deposition processes from one surface
- ❑ 3-dimensional structure built by stacking layers
- ❑ Sacrificial and structural layers used
- ❑ Substrate is usually Si; glass also used
- ❑ SiO_2 and SiN for masking

Wafer Bonding (1)



Wafer Bonding (2)



Smart-Sensor Case Studies

Case Study # 1

Smart Three-Terminal Temperature Sensor
or
Three-Terminal IC Temperature Sensor
or
Voltage-Output IC Temperature Sensor

LM35/LM34

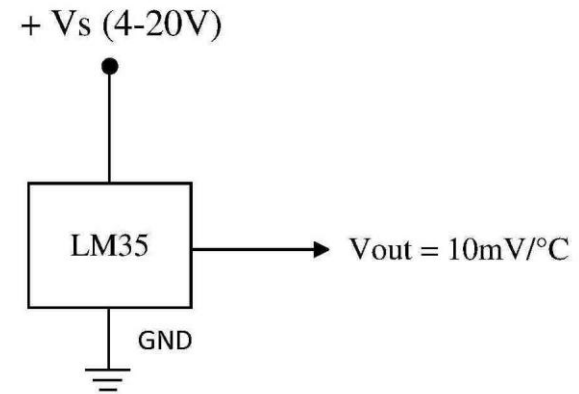
Manufacturer: National Semiconductor Corporation

Website: www.national.com

Major Specifications

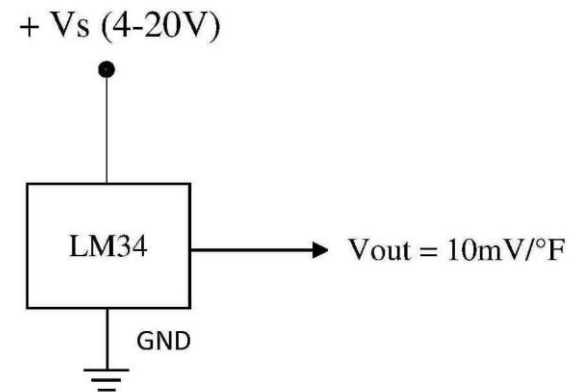
□ LM35: Centigrade (or Celcius) Temperature Sensor

- Range: -55 to +150 °C
- Output (Sensitivity): 10 mV/°C
- Accuracy: ±0.2 °C (typical)
- Linearity: ±0.2 °C (typical)
- Current Drain: 65 μA (typical)



□ LM34: Fahrenheit Temperature Sensor

- Range: -50 to + 300 °F
- Output (Sensitivity): 10 mV/°F
- Accuracy: ±0.4 °F (typical)
- Linearity: ±0.3 °F (typical)
- Current Drain: 75 μA (typical)

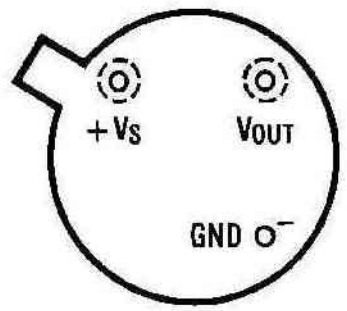


Principle of LM35/LM34

- ❑ These sensors are based on temperature sensitivity of band gap voltage of silicon junction.
- ❑ Band gap (or energy gap) is the energy range in a solid where no free electron states can exist.
- ❑ Band gap in a semiconductor will decrease as its temperature is raised.
- ❑ This property (temperature sensitivity) of semiconductors forms the basis of all silicon temperature sensors.

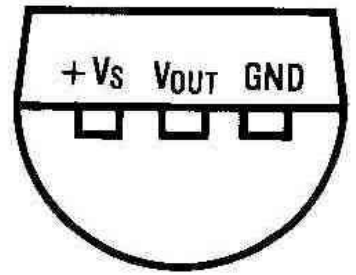
Packages and Pins of LM35

**TO-46
Metal Can Package***



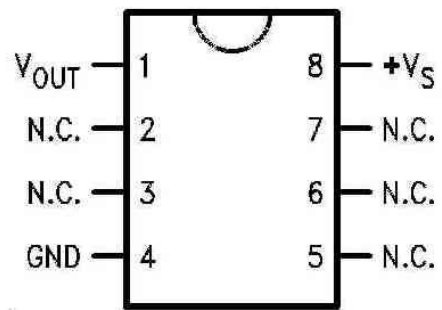
BOTTOM VIEW

**TO-92
Plastic Package**

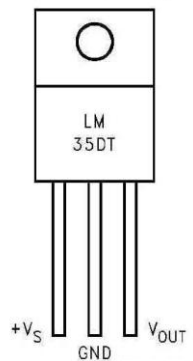


BOTTOM VIEW

**SO-8
Small Outline Molded Package**



**TO-220
Plastic Package***



Case Study # 2

Smart Humidity and Temperature Sensor

SHT7x / SHT1x

Manufacturer: Sensirion Corporation

Website: www.sensirion.com

Salient Features

- ❑ Senses relative humidity and temperature
- ❑ Single chip sensor-cum-transmitter
- ❑ Capacitive polymer sensing element for relative humidity
- ❑ Band-gap for temperature sensing
- ❑ CMOS & micromachining technologies combined
- ❑ Patented as “CMOS Sens” Technology
- ❑ Serial digital output
- ❑ Self calibration

Devices in SHTxx Series

Pin-Type Package

SHT 71

SHT 75



SMD Package

SHT 10

SHT 11

SHT 15

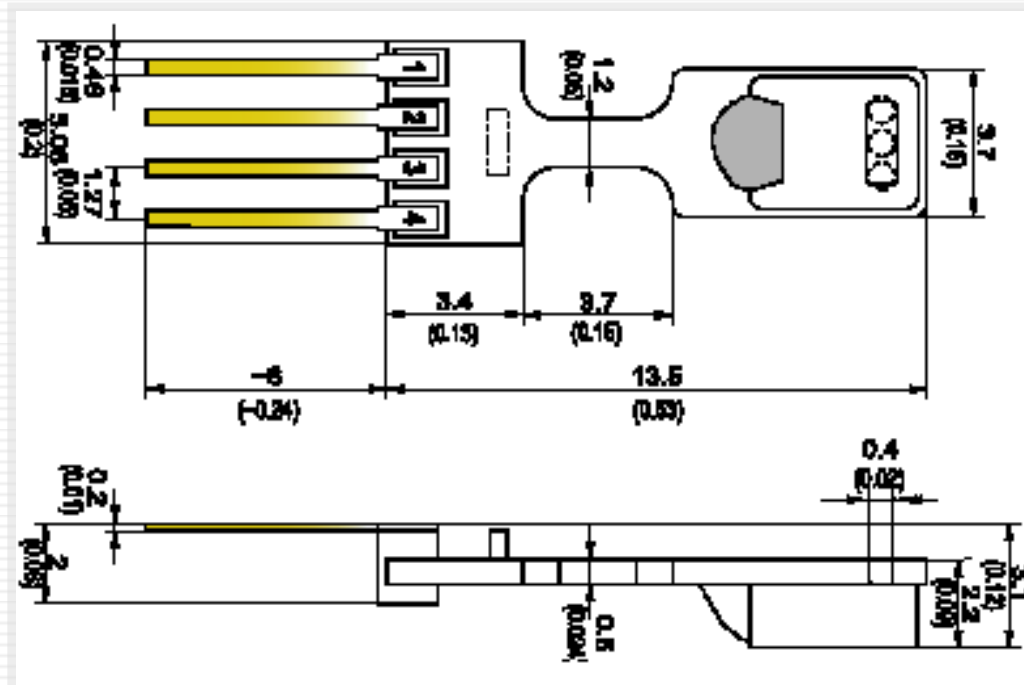


Technical Data

Feature	SHT 71	SHT 75	SHT 10	SHT 11	SHT 15
RH Accuracy	± 3%	± 1.8%	± 4.5%	± 3%	± 2%
RH Range	0-100%			0-100%	
RH Stability	<0.5% per year		<0.5% per year		
Temp. Accuracy @ 25°C	0.4°C	± 0.3°C	±0.5°C	±0.4°C	0.3°C
Temp. Range	-40 to + 120°C		-40 to + 120°C		
Power Consumption	30μW	20μW	30μW	30μW	30μW
Response Time	4s		4s		
Package	4-Pin SIL		SMD (LCC)*		

**Surface mounting device (leadless chip carrier)*

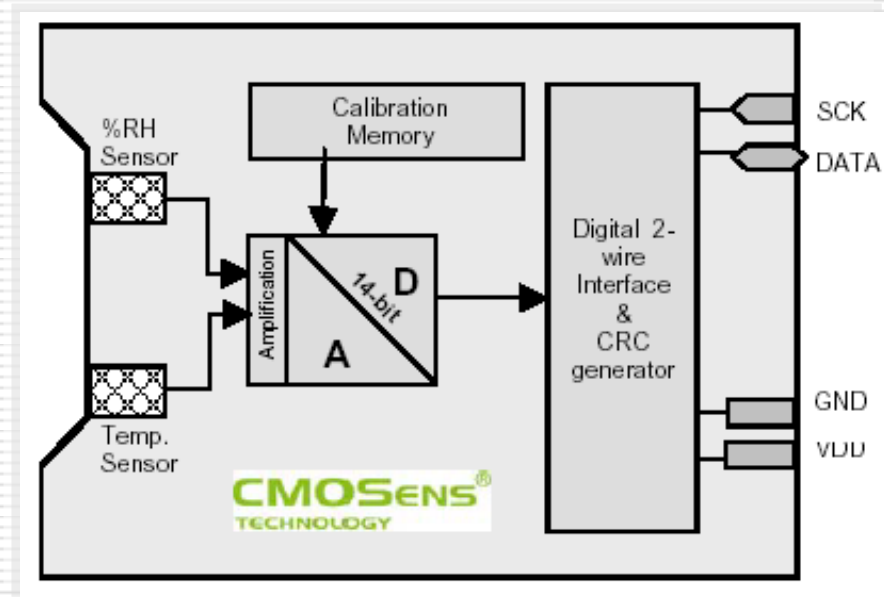
Dimensions of SHT7x



(Source: Data sheet of SHTxx)

Block Diagram

Pin No.	Pin Name	Description
1	SCK	Serial clock input
2	VDD	Supply 2.4 – 5.5 V
3	GND	Ground
4	DATA	Serial data bidirectional



Serial interface of SHTxx is not compatible with I²C interfaces.

Case Study # 3

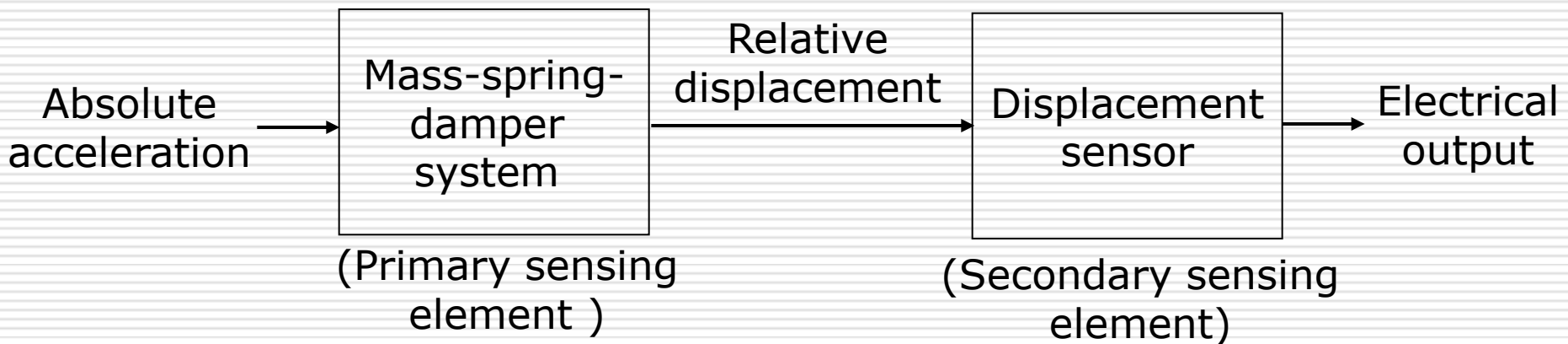
Smart Acceleration Sensor or iMEMS Accelerometer

**ADXL
150/250/210/311**

Manufacturer: Analog Devices

Website: www.analog.com

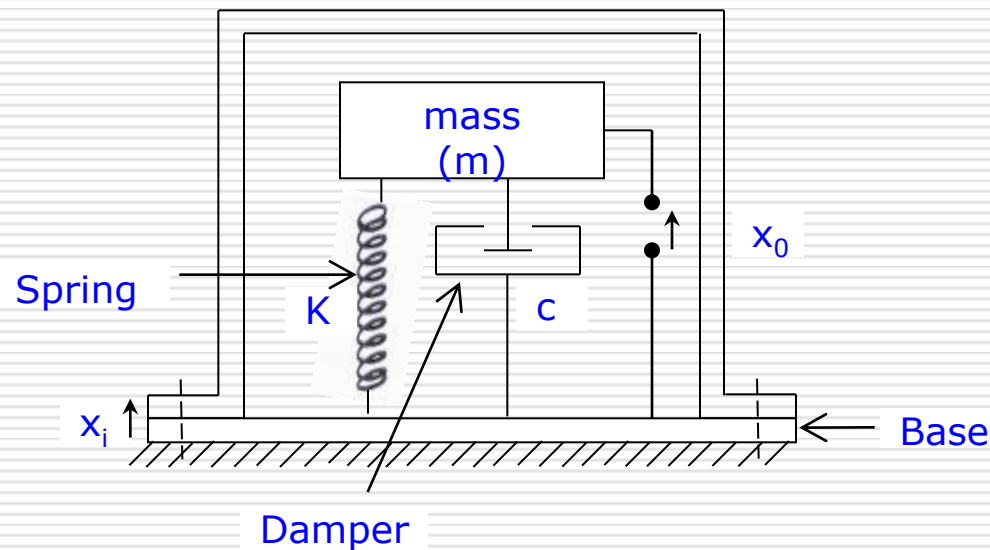
Basic Principle of Acceleration Sensors



Displacement Sensor Options

- (a) Strain gauge: Output is change in resistance
- (b) Capacitive displacement sensor: Output is change in capacitance
- (c) Piezoelectric transducer: Output is electric charge

Mass-Spring-Damper (MSD) System



m = mass in kg

c = damping constant in Ns/m

k = spring stiffness in N/m

Frequency Response of MSD System

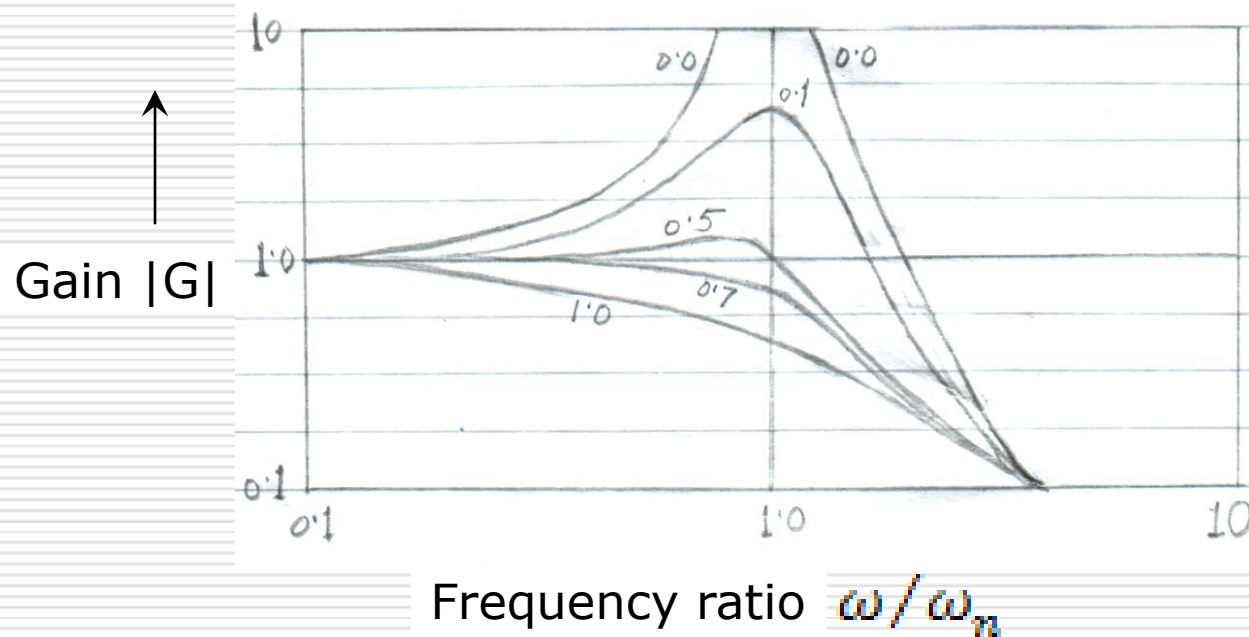
$$G(j\omega) = \frac{1/\omega_n^2}{1 + \left(j\omega/\omega_n\right)^2 + 2j\xi(\omega/\omega_n)}$$

where G is the ratio of relative displacement (output), x_0
to the absolute acceleration (input), x_i ,

ω_n is the natural frequency , and

ξ is the damping ratio.

Frequency Response Plot of MSD System



Smart Acceleration Sensors: ADXL Series

□ **ADXL 150: Single-axis**

14-Pin dual-in-line (DIL) package

DC output

□ **ADXL 250: Dual-axis**

14-Pin dual-in-line (DIL) package

DC output

□ **ADXL 210: Dual-axis**

8-Terminal leadless chip carrier (LLC) package

PWM output

□ **ADXL 311: Dual-axis**

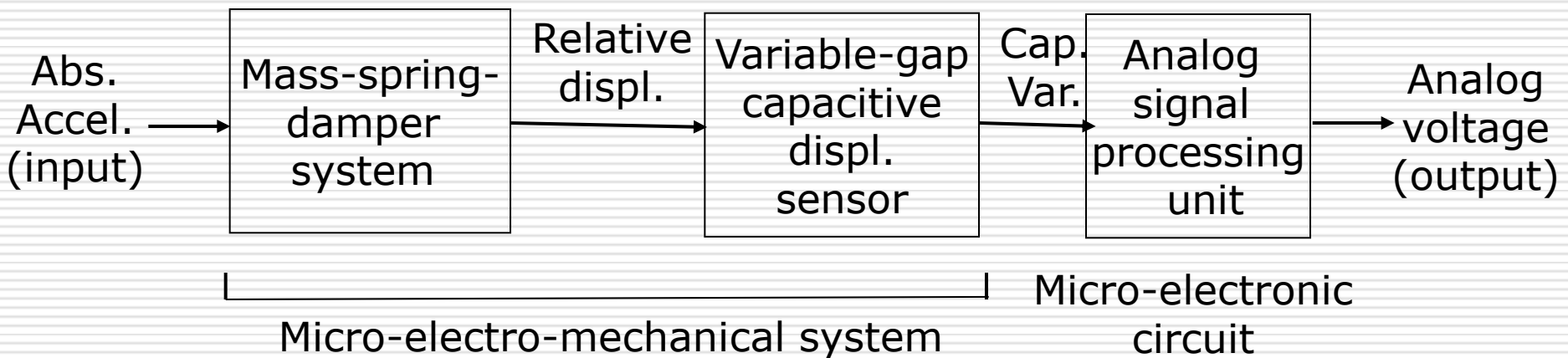
8-Terminal leadless chip carrier (LLC) package

DC output

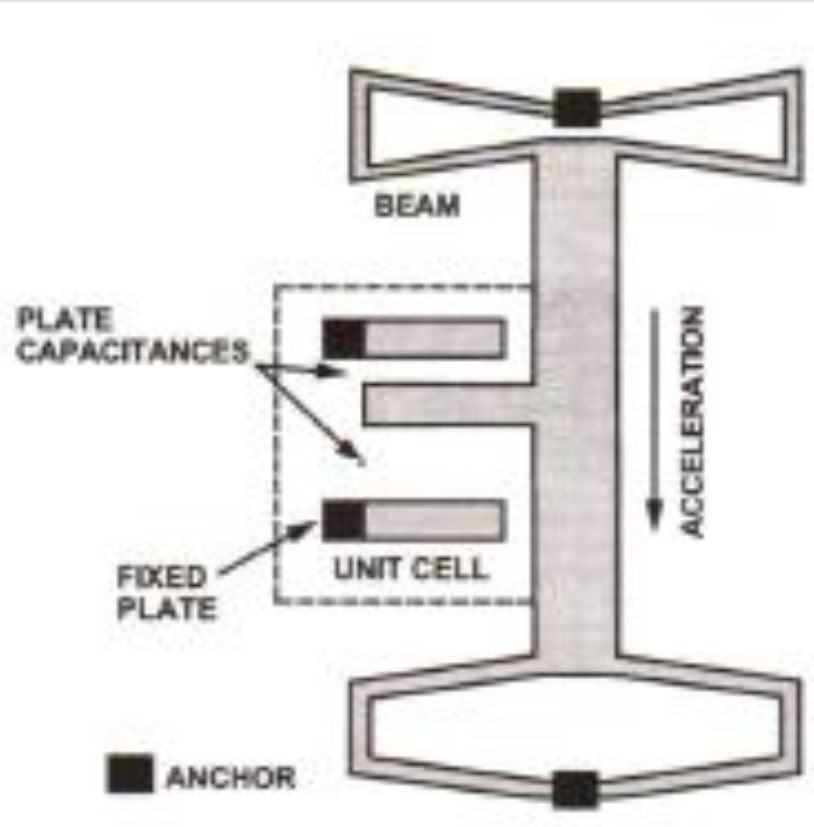
Common Features of ADXL Series

- ❑ Can measure dynamic acceleration (vibrations) as well as static acceleration (gravity)
- ❑ Ultra-small package
- ❑ Ultra-low weight (<1 gram)
- ❑ Low power (<0.5 mA @ Vs)
- ❑ Output is ratiometric to supply voltage
- ❑ Self test feature
- ❑ 1000 g shock survival
- ❑ Sensing element fabricated using proprietary surface micromachining process.

Block Schematic of ADXL-150

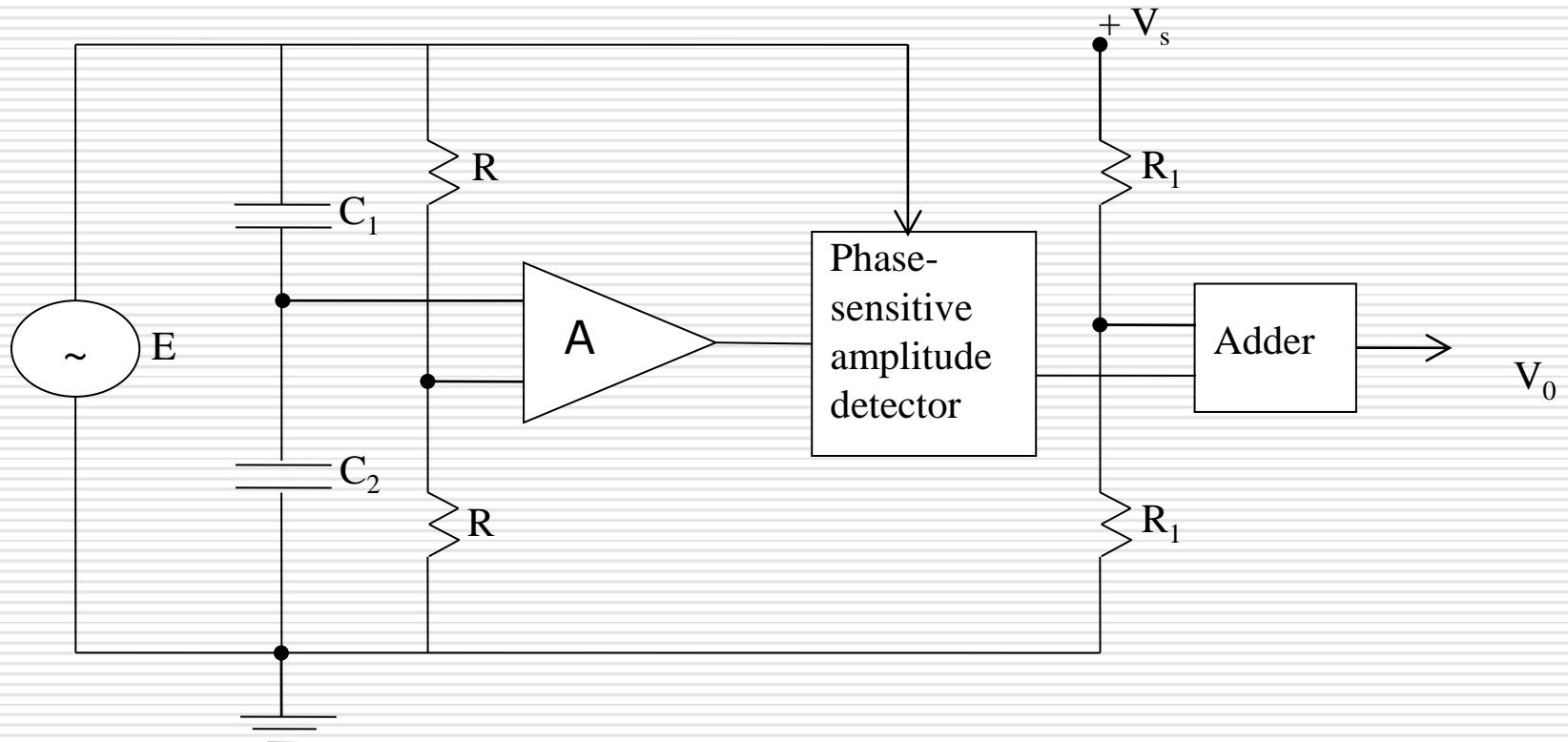


Sensor (MEMS) of ADXL



(Source: Data sheets of ADXL-150)

ASPU of ADXL-150



For acceleration = 0, $C_1 = C_2 = C$

For acceleration = a , $C_1 = C + \Delta C$ & $C_2 = C - \Delta C$

For acceleration = $-a$, $C_1 = C - \Delta C$ & $C_2 = C + \Delta C$

Output of ADXL-150

- The output of signal processing circuit is a d.c. voltage
- It is ratiometric and given by

$$V_0 = \frac{V_s}{2} + S.a. \frac{V_s}{5}$$

- Here

V_0 = output voltage

V_s = supply voltage (actual)

S = sensitivity of the smart sensor in V/g @ 5V

a = acceleration in g

- The maximum value of $S.a. \frac{V_s}{5}$ is less than $\pm V_s/2$.
- Therefore, the sensor output V_0 is always positive.

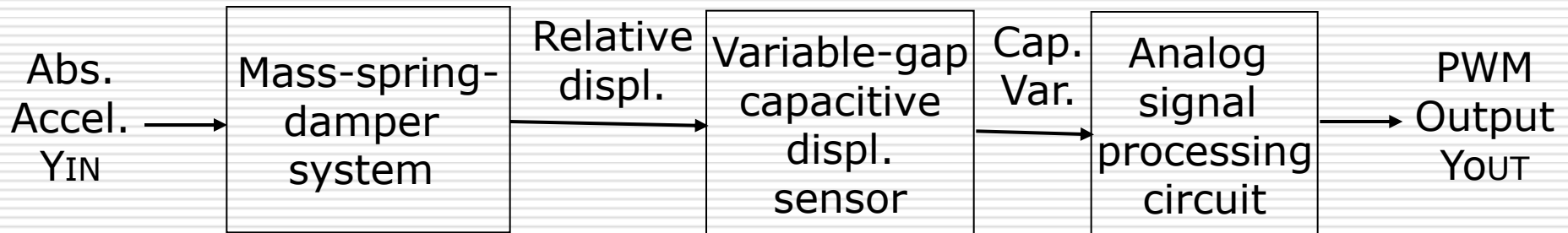
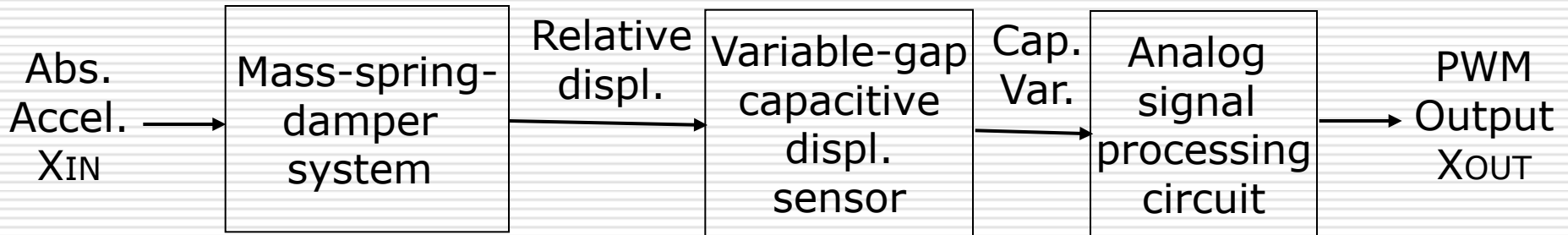
Specifications of ADXL-150

Input Range	:	$\pm 50 \text{ g}$
Power Supply (V_s)	:	4.0 V to 6.0 V
Sensitivity @ $V_s = 5\text{V}$:	38 mV/g
Transverse Sensitivity	:	$\pm 2\%$
Zero-g offset	:	$0.5 V_s$
Output Swing	:	0.25 V to $V_s - 0.25 \text{ V}$
Sensor Resonant Freq.	:	24 kHz
3dB Bandwidth	:	1 kHz
Output change on Self Test	:	0.25 to 0.60 V
Operating Temperature	:	0 to 70°C

Important Features of ADXL-210E

- ❑ **Dual-axis sensor** on a single IC chip
- ❑ Ultra-small chip (5x5x2 mm)
- ❑ **PWM output**, allowing direct interface to low-cost microcontrollers
- ❑ Adjustable duty cycle period (0.5 – 1.0 ms)
- ❑ Wide operating voltage range (3V - 5.25V)

Block Schematic of ADXL-210E



Case Study # 4

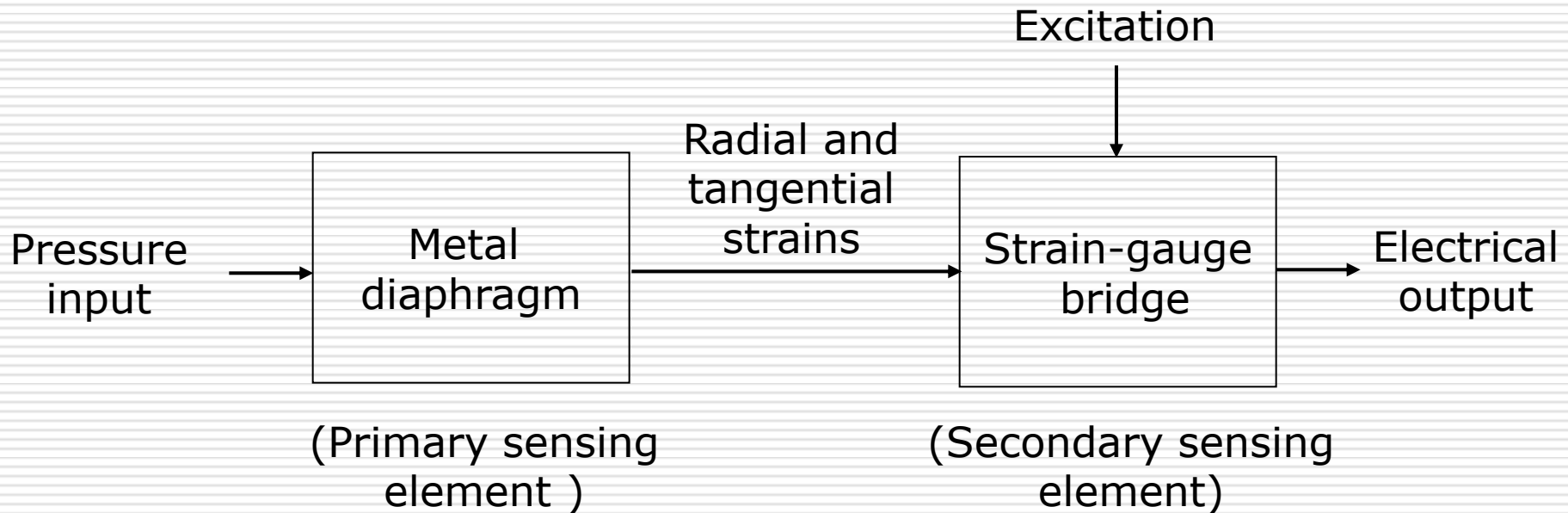
Smart Pressure Sensor or Integrated Silicon Pressure Sensor

MPX5700 Series

Manufacturer: Freescale Semiconductor Inc.

Website: www.freescale.com

Principle of Conventional Pressure Sensor of Diaphragm Type using Strain Gauges



Salient Features of MPX5700

- ❑ Monolithic silicon pressure sensor
- ❑ Diaphragm based piezo-resistive sensor
- ❑ High-level analog output signal
- ❑ **Combines micromachining, bipolar IC and thin-film metallization techniques**
- ❑ **Available for absolute, differential and gauge pressure measurements**

Variants of MPX5700

□ MPX5700A

- Smart **absolute** pressure sensor
- Has single pressure port

□ MPX5700D

- Smart **differential** pressure sensor
- Has two pressure ports

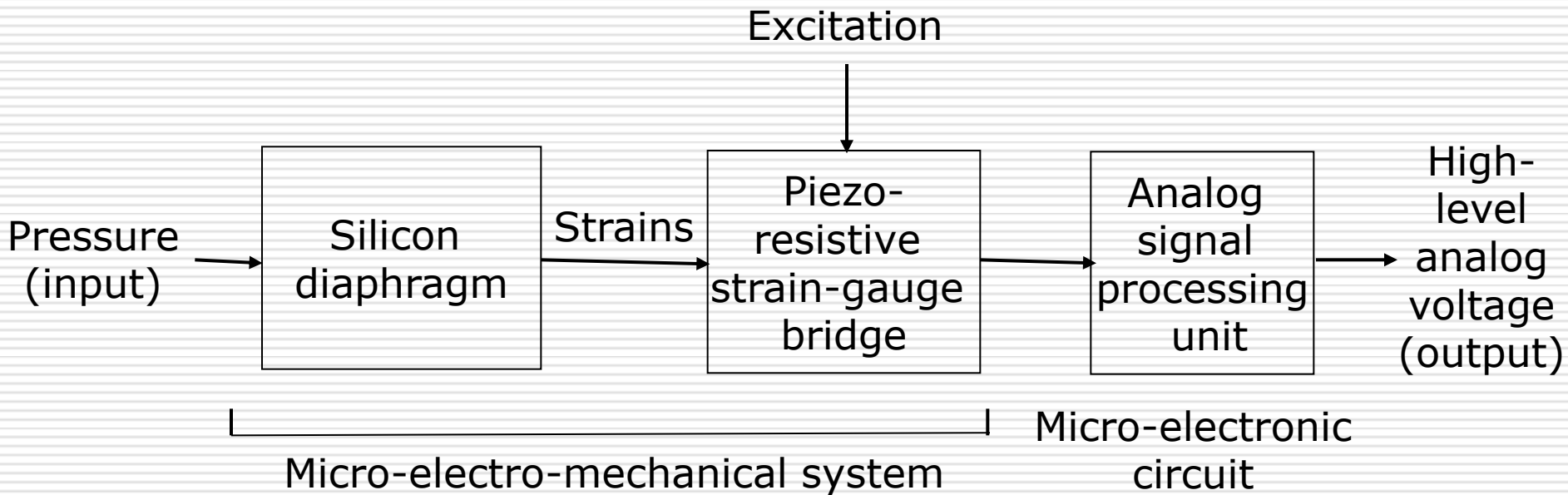
□ MPX5700G

- Smart **gauge** pressure sensor
- Has single pressure port

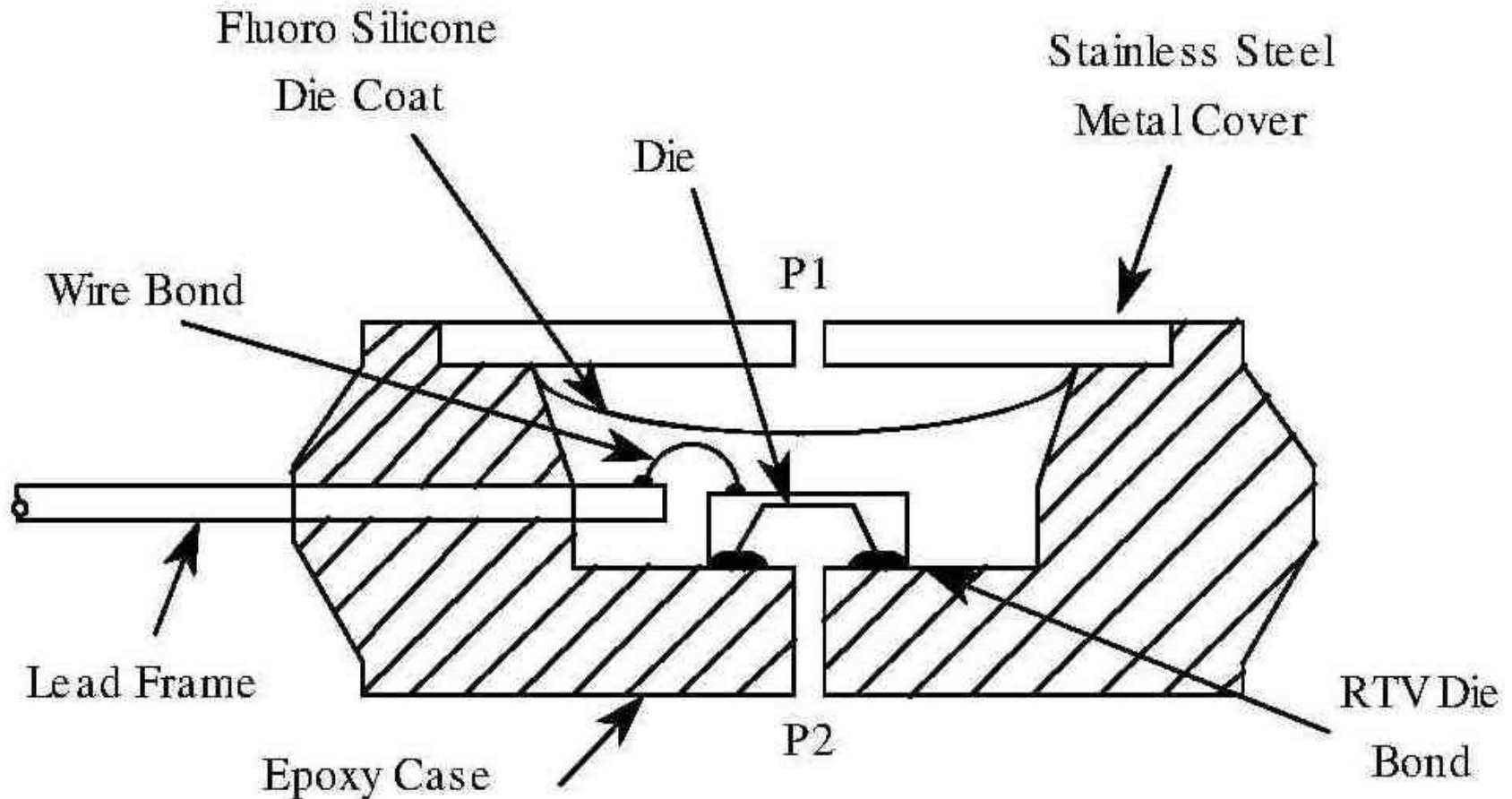
Operating Characteristics of MPX5700

S. No.	Characteristic	Value
1	Pressure Range for Gauge/Differential sensors	0 – 700 kPa
2	Pressure Range for Absolute pressure sensors	15 – 700 kPa
3	Supply Voltage	5.0 ± 0.25V Vdc
4	Full Scale Output	4.7 Vdc
5	Accuracy	±2.5 %V _{FSS}
6	Sensitivity	6.4 mV/kPa
7	Response Time for 10% to 90% change	1.0 ms
8	Warm-Up Time	20 ms

Block Schematic of MPX5700



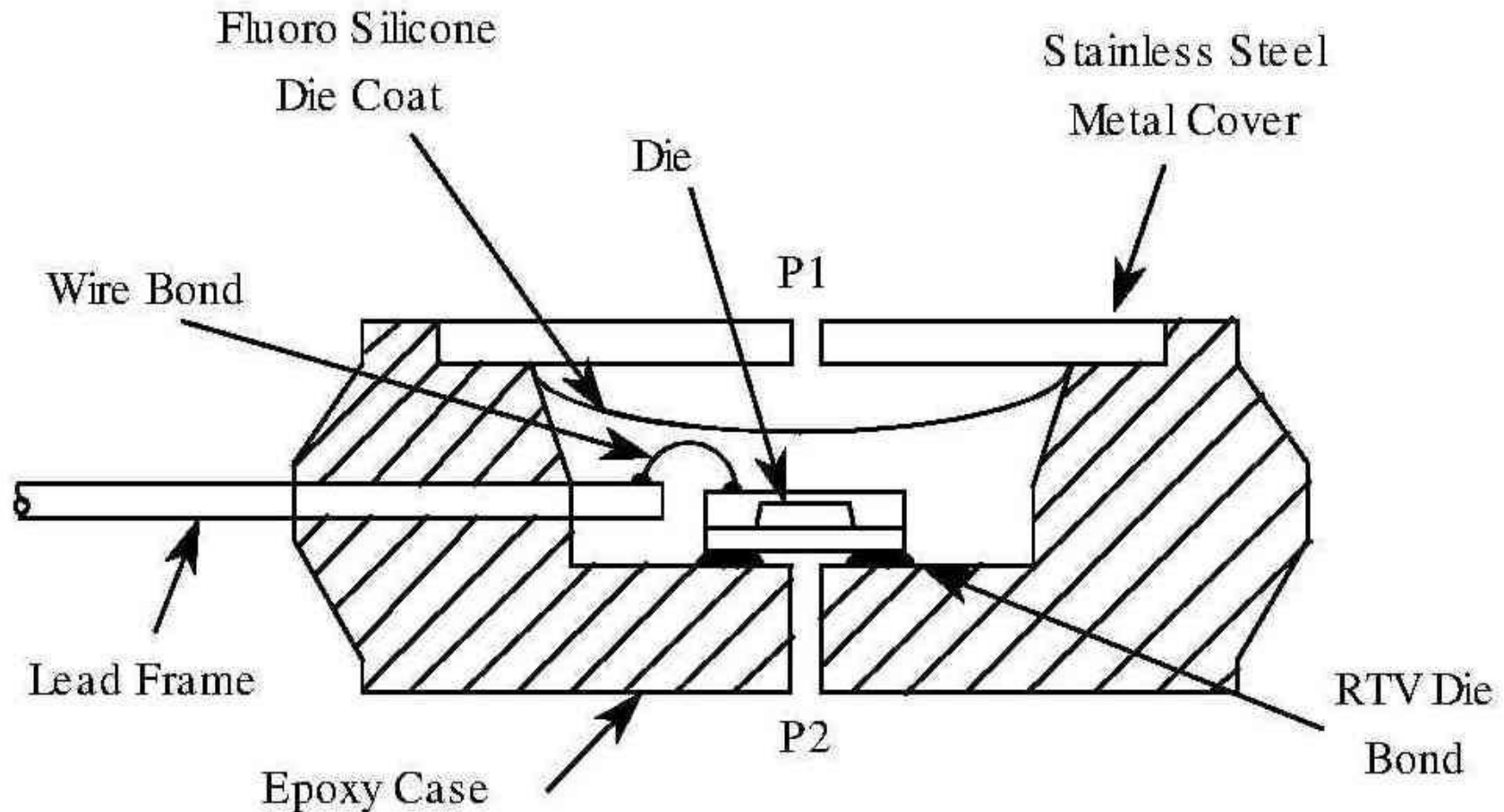
Construction: Cross-Sectional Diagram of Differential/Gauge Pressure Sensing Element



DIFFERENTIAL/GAUGE ELEMENT

(Source: Data sheet of MPX5700)

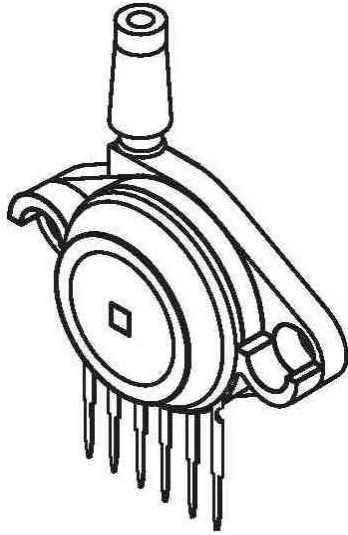
Construction: Cross-Sectional Diagram of Absolute Pressure Sensing Element



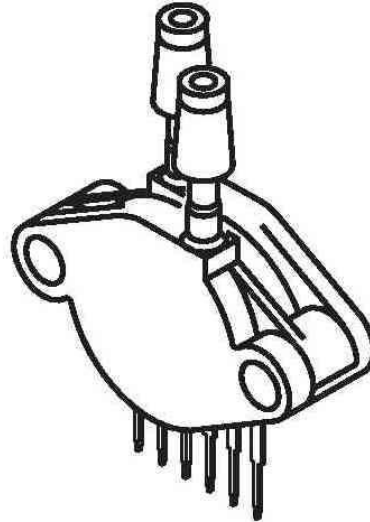
ABSOLUTE ELEMENT

(Source: Data sheet of MPX5700)

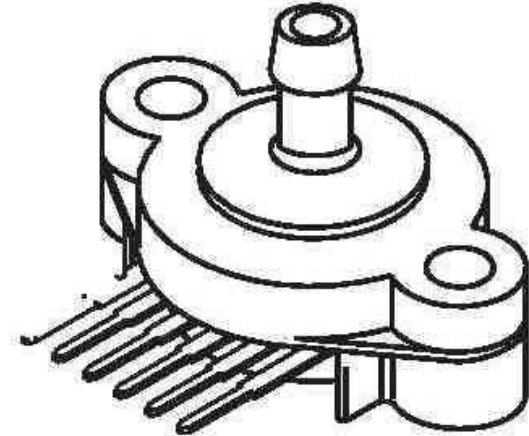
Packages and Pins



**MPX5700AP/GP/GP1
CASE 867B-04**



**MPX5700DP
CASE 867C-05**



**MPX5700ASX
CASE 867F-03**

PIN 1: V_{OUT}

PIN 4: V_1

PIN 2: GROUND

PIN 5: V_2

PIN 3: V_{CC}

PIN 6: V_{EX}

(Source: Data sheet of MPX5700)

Thank you!